

## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior listing of claims in the application.

1. (Cancelled)

2.(Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein said metal overburden is selected from copper, tantalum, silicon dioxide, or mixtures thereof.

3. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein said metal overburden is copper.

4. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein said second slurry is abrasive free.

5. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein said abrasive of said first slurry is selected from alumina, titania, zirconia, gennania, silica, ceria, or mixtures thereof.

6. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein said metal overburden wherein said abrasive of said first slurry is silica.

7. (Currently Amended) The method ~~slurry system~~ of claim 4 wherein said abrasive of said first slurry is precipitated silica.

8. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein said abrasive is present in an amount of from 0.1 to 30 percent by weight of said first slurry.

9. (Currently Amended) The method ~~slurry system~~ of claim ~~6~~ 4 wherein said silica has an aggregate of primary particles, said primary particles having an average diameter of at least seven (7) nanometers, wherein said aggregate has an aggregate size of less than one (1) micron, and a hydroxyl content of at least seven (7) hydroxyl groups per nanometer squared.

10. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein at least one of said first and second slurries further comprise an oxidant.

11. (Currently Amended) The method ~~slurry system~~ of ~~claim 8~~ claim 10 wherein said oxidant is selected from inorganic and organic per-compounds, bromic acid, chloric acid, nitrates, sulfates, or mixtures thereof.

12. (Currently Amended) The method ~~slurry system~~ of ~~claim 8~~ claim 10 wherein said oxidant is selected from hydrogen peroxide, urea-hydrogen peroxide, or mixtures thereof.

13. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein at least one of said first and second slurries further comprise a material selected from complexing agent, anticorrosion agent, stopping compound, polyvalent cation sequestrant, thickener, or mixtures thereof.

14. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein at least one of said first and second slurries further comprises an acid selected from picolinic acid, dipicolinic acid, quolinic acid, and mixtures thereof.

15. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein at least one of said first and second slurries further comprises a polyvalent cation sequestrant and a anticorrosion agent.

16. (Currently Amended) The method ~~slurry system~~ of ~~claim 1~~ claim 24 wherein at least one of said first and second slurries further comprises a polyvalent cation sequestrant, a anticorrosion agent, and a thickener.

17.-20. (Cancelled)

21. (Currently Amended, Withdrawn) A method for removal of a copper overburden on a microelectronic substrate, said method comprising the steps of:

(a) applying to a substrate a first slurry which comprises an abrasive for a first polishing of the copper overburden;

(b) terminating the first polishing step of (a) prior to removal of the entire copper overburden leaving residual copper overburden on the substrate; and

(c) applying to said substrate a second slurry, wherein said first slurry has higher concentration of said abrasive than said second slurry, and wherein the second polishing step is performed to remove the residual copper overburden of the substrate.

22.-23. (Cancelled)

24. A method for polishing a microelectronic substrate to remove a metal overburden of the microelectronic substrate comprising the steps of:

(a) performing a first polish with a first slurry and polishing pad, wherein said first slurry comprises abrasive; and

(b) terminating the first polishing step of (a) prior to removal of the entire metal overburden leaving residual metal overburden on the substrate; and

(c) performing a second polish with a second slurry and polishing pad wherein said first slurry has higher concentration of said abrasive than said second slurry, and wherein the second polishing step is performed to remove the residual metal overburden of the substrate.

25.-26. Cancelled.

27. (Currently Amended) The method of claim 24 ~~25~~ wherein said metal is selected from copper, tantalum and silicon dioxide.

28. (Original) The method of claim 24 wherein said first polish is completed prior to applying said second slurry.

29. (Original) The method of claim 24 further comprising the step of washing said substrate after completion of said first polish and prior to initiation of said second polish.